

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	18mΩ@10V	7A
	24mΩ@4.5V	
-30V	19mΩ@-10V	-8A
	25mΩ@-4.5V	



合肥矽普半导体

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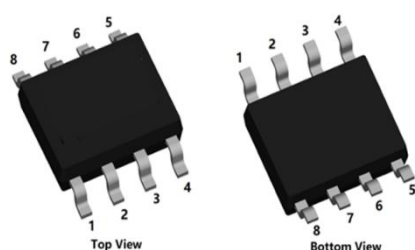
Feature

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- 100% Single Pluse avalanche energy Test

Applications

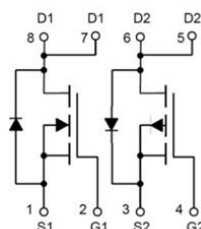
- Battery Protection
- Load Switch
- Power Management

Package

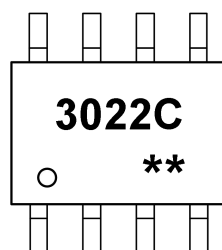


SOP-8L

Circuit diagram



Marking



3022C
**

:Device Code
:Week Code

Order Information

Device	Package	Unit/Tape
SP3022CP8	SOP-8L	4000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value		Units
		N-Channel	P-Channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	7	-8	A
Pulsed Drain Current	I_{DM}	28	-32	A
Single Pulse Avalanche Energy ¹	E_{AS}	10.5	30	mJ
Power Dissipation	P_D	1.8		W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	69.5		°C/W
Storage Temperature Range	T_{STG}	-55 to 150		°C
Operating Junction Temperature Range	T_J	-55 to 150		°C

N-Channel Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	30	-	-	V
Drain-Source Leakage Current	IDSS	VDS=24V , VGS=0V , TJ=25℃	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	1	1.6	2.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=8A	-	18	28	mΩ
		VGS=4.5V , ID=6A	-	24	35	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=15V , VGS=0V , f=1MHz	-	416	-	pF
Output Capacitance	Coss		-	62	-	
Reverse Transfer Capacitance	Crss		-	51	-	
Total Gate Charge	Qg	VDS=20V , VGS=4.5V , ID=6A	-	5	-	nC
Gate-Source Charge	Qgs		-	1.11	-	
Gate-Drain Charge	Qgd		-	2.61	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=12V, VGS=10V , RG=3Ω, ID=6A	-	7.7	-	nS
Rise Time	Tr		-	46	-	
Turn-Off Delay Time	Td(off)		-	11	-	
Fall Time	Tf		-	3.6	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	7	A
Reverse Recovery Time	Trr	Is=10A, di/dt=100A/us, Tj=25℃	-	18	-	nS
Reverse Recovery Charge	Qrr		-	2	-	nC

Note :

1. The EAS test condition is $V_{DD}=15V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

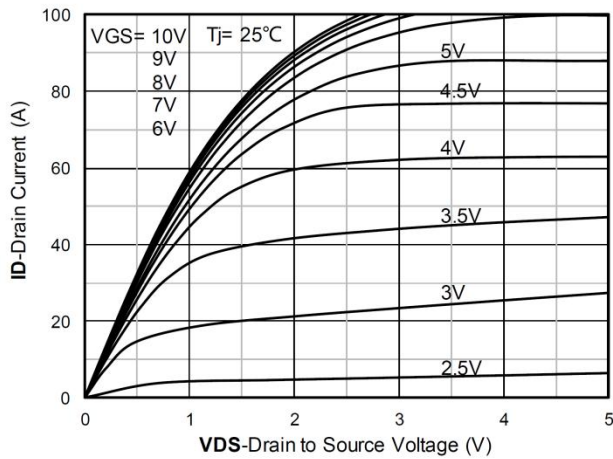
P-Channel Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=-250uA	-30	-	-	V
Drain-Source Leakage Current	IDSS	VDS=-24V , VGS=0V , TJ=25℃	-	-	-1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =-250uA	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=-10V , ID=-8A	-	19	28	mΩ
		VGS=-4.5V , ID=-6A	-	25	35	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=-15V , VGS=0V , f=1MHz	-	1070	-	pF
Output Capacitance	Coss		-	146	-	
Reverse Transfer Capacitance	Crss		-	142	-	
Total Gate Charge	Qg	VDS=-30V , VGS=-10V , ID=-6A	-	21	-	nC
Gate-Source Charge	Qgs		-	2.1	-	
Gate-Drain Charge	Qgd		-	5.6	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=-15V VGS=-10V , RG=6Ω, ID=-1A	-	7	-	nS
Rise Time	Tr		-	9	-	
Turn-Off Delay Time	Td(off)		-	30	-	
Fall Time	Tf		-	18	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=-1A , TJ=25℃	-	-	-1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	-8	A
Reverse Recovery Time	Trr	Is=-20A, di/dt=-100A/us, Tj=25℃	-	50	-	nS
Reverse Recovery Charge	Qrr		-	31	-	nC

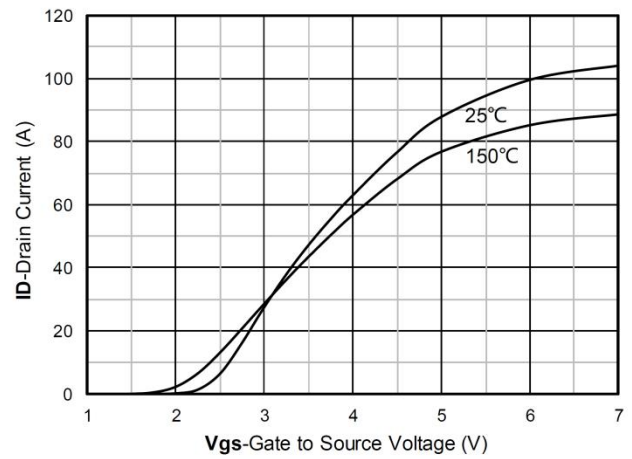
Note :

1. The EAS test condition is $V_{DD}=-15V$, $V_{GS}=-10V$, $L=0.5mH$, $R_G=25\Omega$

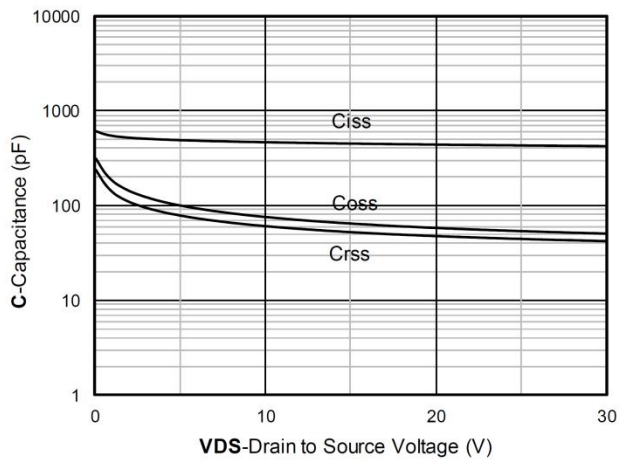
N-Channel Typical Characteristics



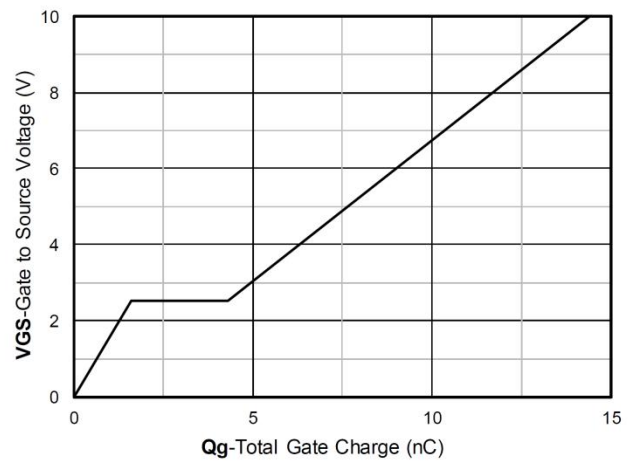
Output Characteristics



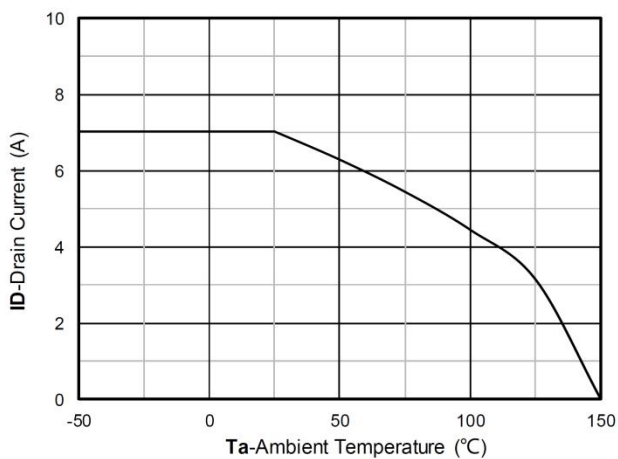
Transfer Characteristics



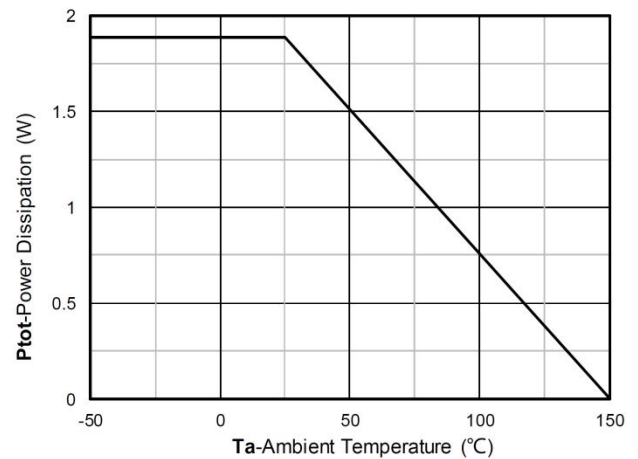
Capacitance Characteristics



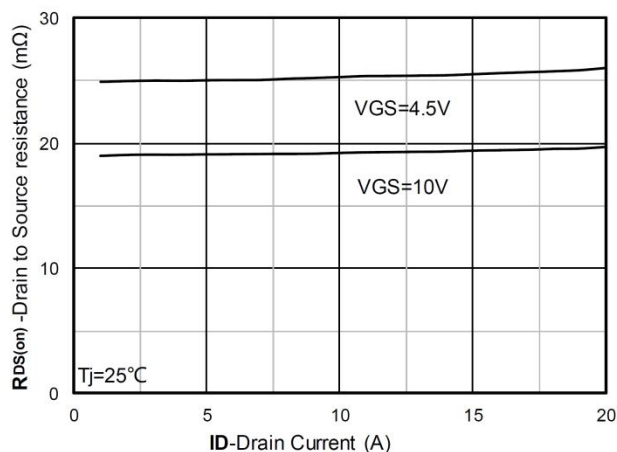
Gate Charge



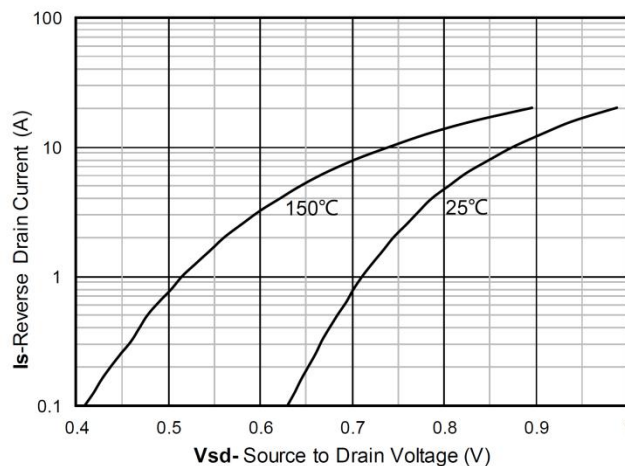
Current dissipation



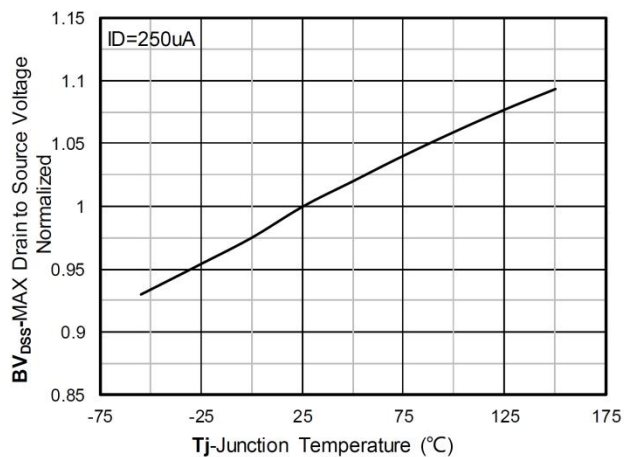
Power dissipation



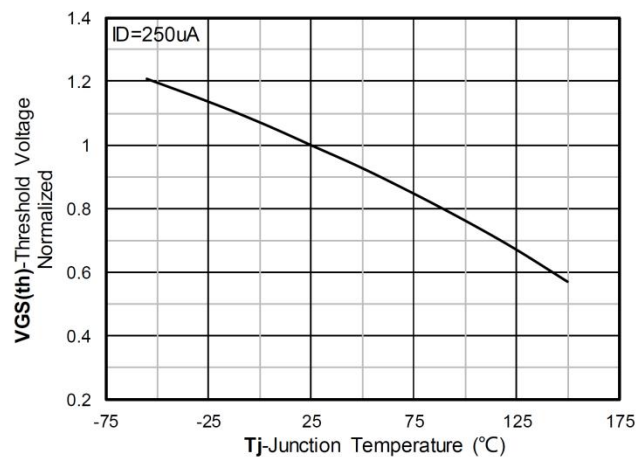
RDS(on) VS Drain Current



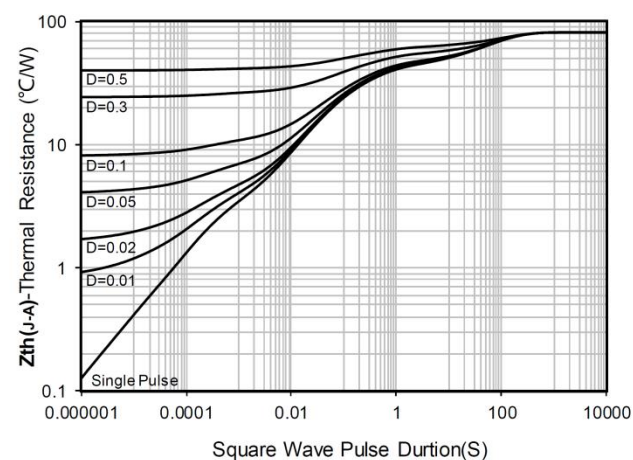
Forward characteristics of reverse diode



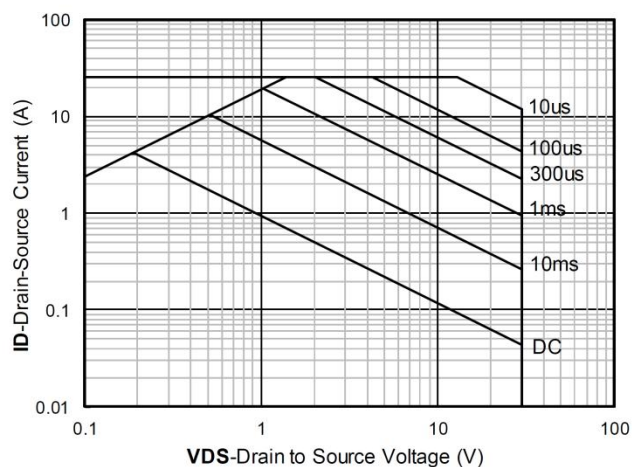
Normalized breakdown voltage



Normalized Threshold voltage

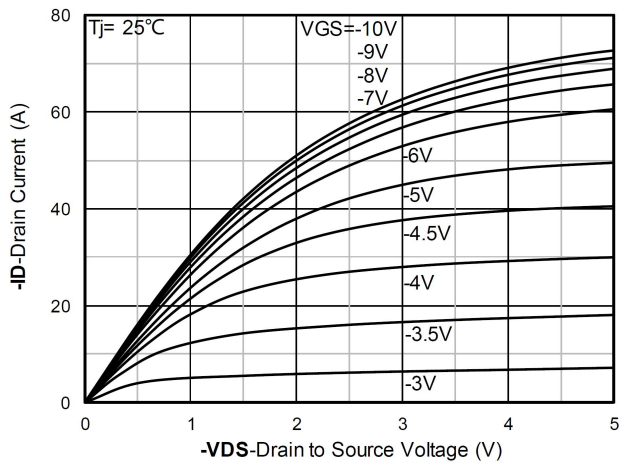


Maximum Transient Thermal Impedance

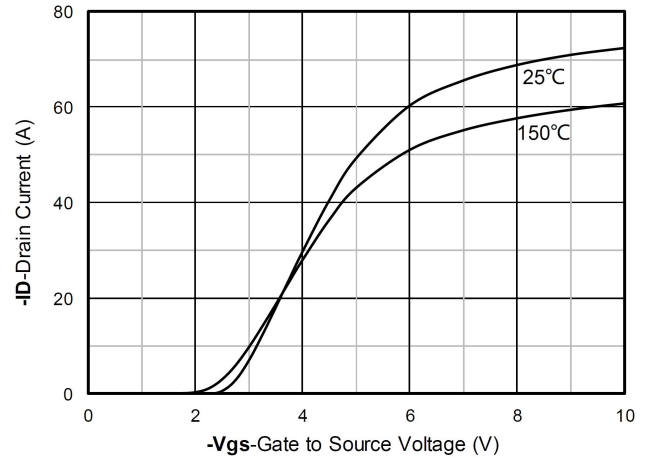


Safe Operation Area

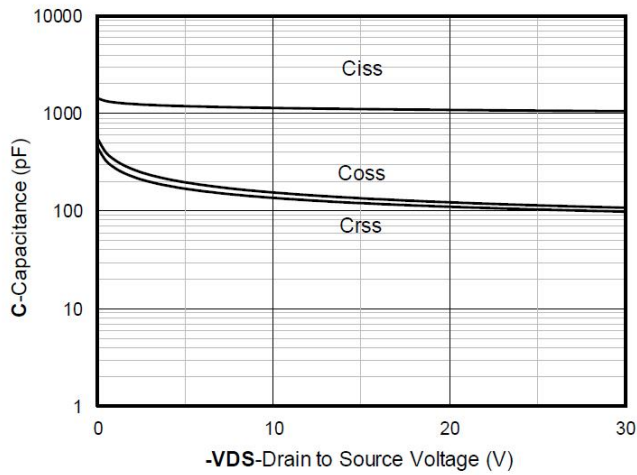
P-Channel Typical Characteristics



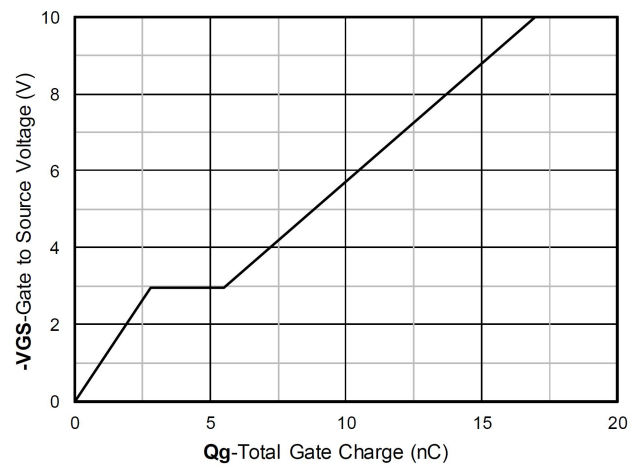
Output Characteristics



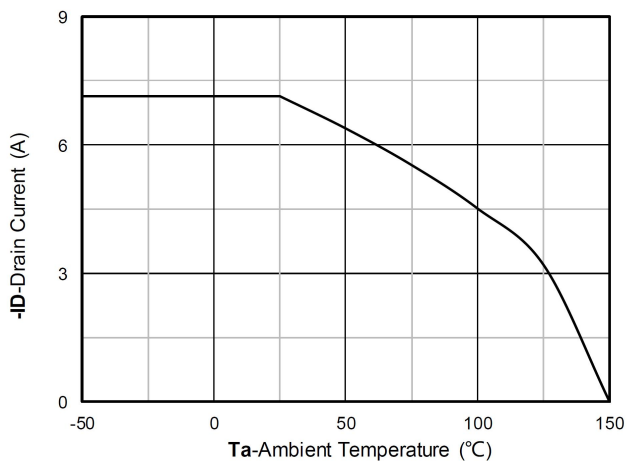
Transfer Characteristics



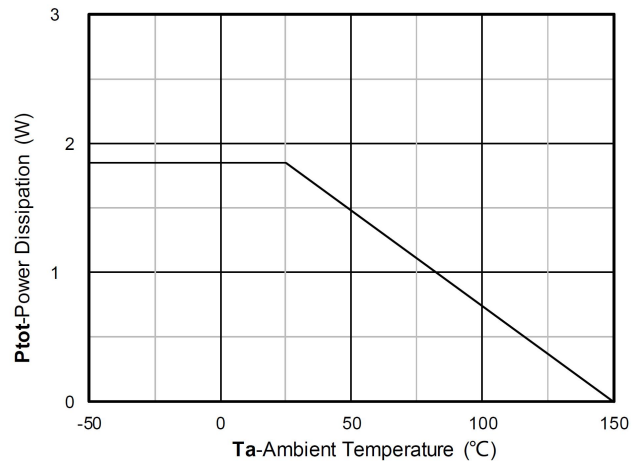
Capacitance Characteristics



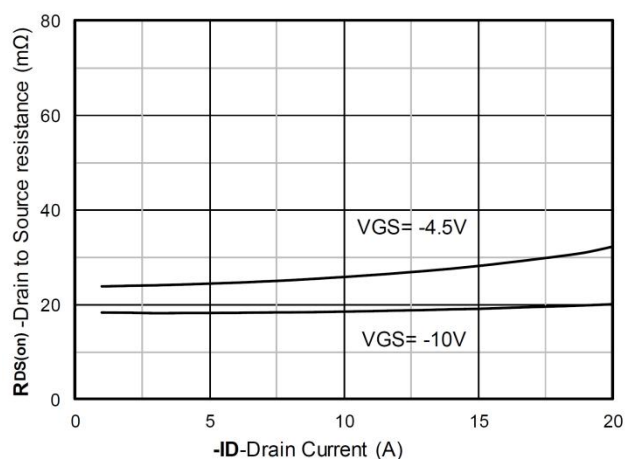
Gate Charge



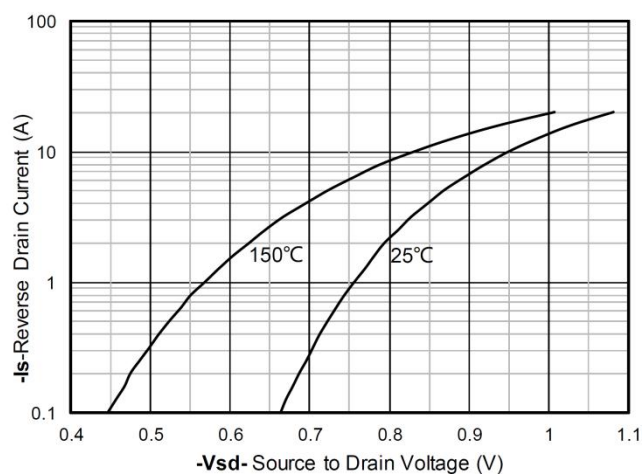
Current dissipation



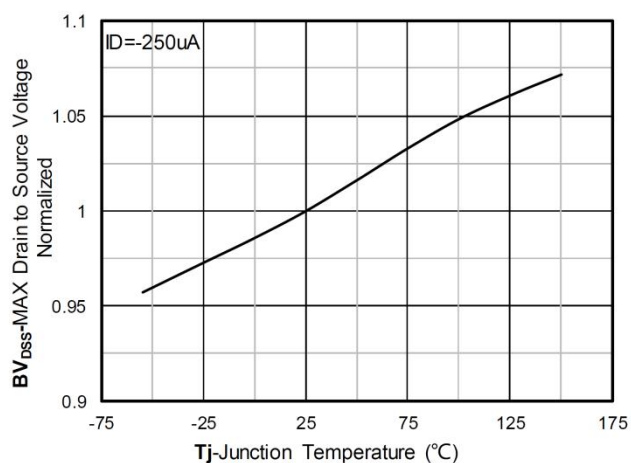
Power dissipation



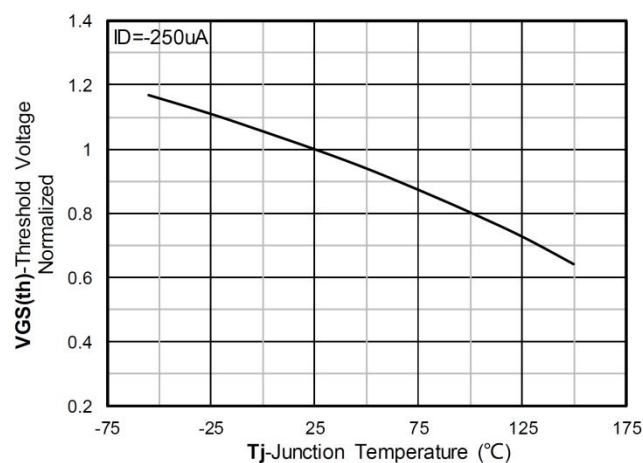
$R_{DS(on)}$ VS Drain Current



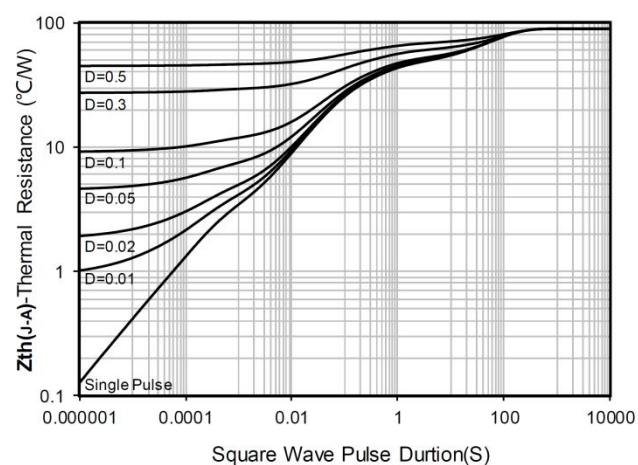
Forward characteristics of reverse diode



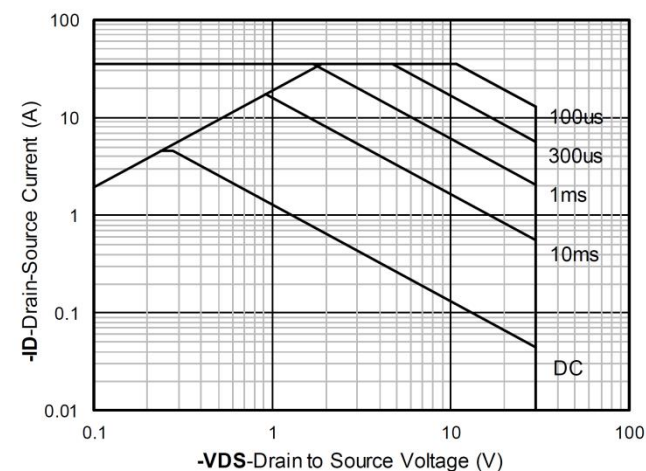
Normalized breakdown voltage



Normalized Threshold voltage

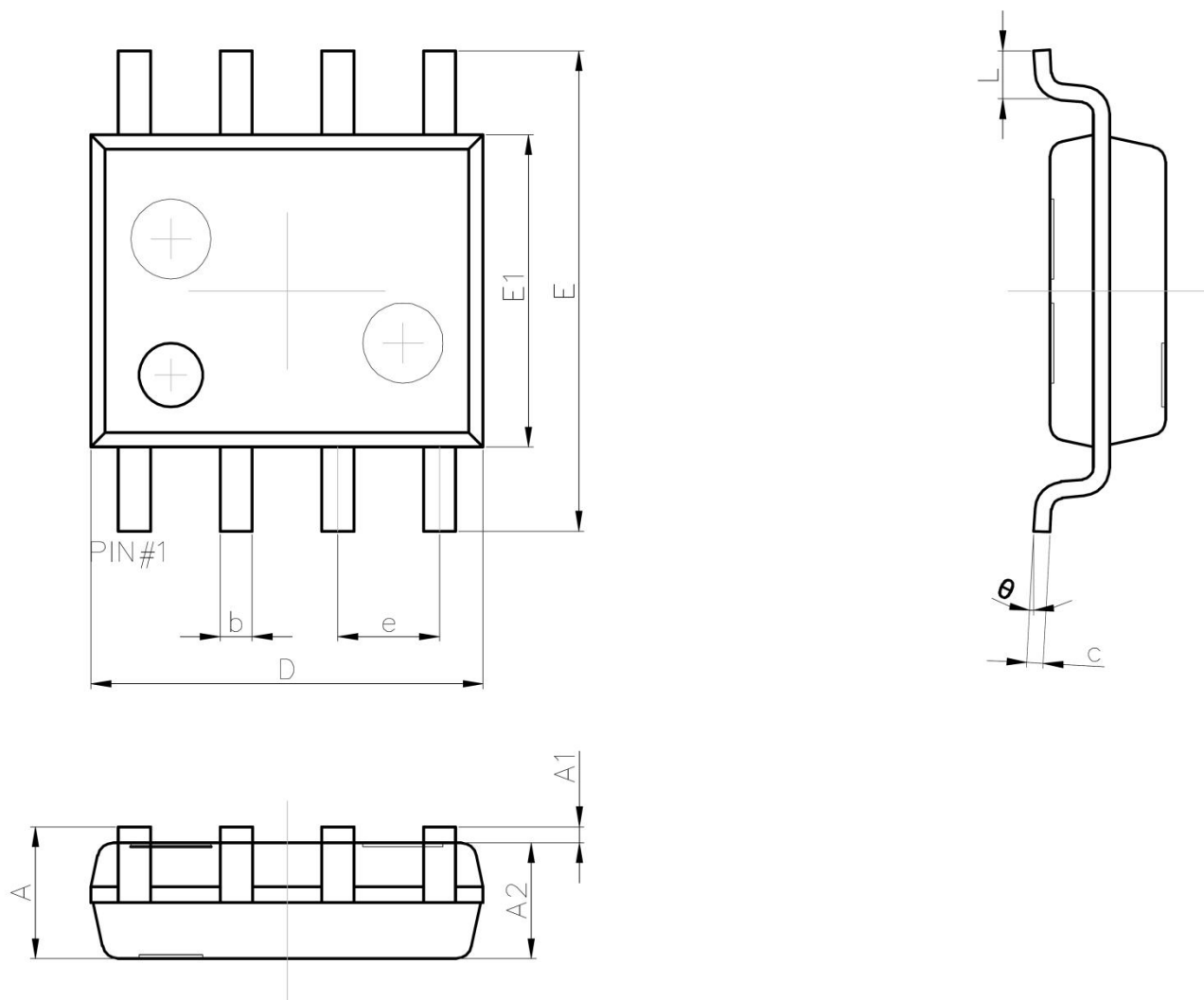


Maximum Transient Thermal Impedance



Safe Operation Area

SOP-8L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°